

High Temperature Silicon Carbide Power Schottky Diode

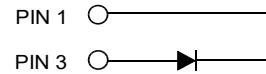
V_{RRM}	=	650 V
$I_F (T_c=25^\circ C)$	=	4 A
Q_c	=	7 nC

Features

- 650 V Schottky rectifier
- 210 °C maximum operating temperature
- Zero reverse recovery charge
- Superior surge current capability
- Positive temperature coefficient of V_F
- Temperature independent switching behavior
- Lowest figure of merit Q_c/I_F
- Available screened to Mil-PRF-19500

Package

- RoHS Compliant



SMD0.5 / TO – 276 (Hermetic Package)

Advantages

- High temperature operation
- Improved circuit efficiency (Lower overall cost)
- Low switching losses
- Ease of paralleling devices without thermal runaway
- Smaller heat sink requirements
- Industry's lowest reverse recovery charge
- Industry's lowest device capacitance
- Ideal for output switching of power supplies
- Best in class reverse leakage current at operating temperature

Applications

- Down Hole Oil Drilling
- Geothermal Instrumentation
- Solenoid Actuators
- General Purpose High-Temperature Switching
- Amplifiers
- Solar Inverters
- Switched-Mode Power Supply (SMPS)
- Power Factor Correction (PFC)

Maximum Ratings at $T_j = 210^\circ C$, unless otherwise specified

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak reverse voltage	V_{RRM}		650	V
Continuous forward current	I_F	$T_c = 25^\circ C$	4	A
Continuous forward current	I_F	$T_c \leq 190^\circ C$	1	A
RMS forward current	$I_{F(RMS)}$	$T_c \leq 190^\circ C$	2	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_c = 25^\circ C, t_p = 10 \text{ ms}$	10	A
Non-repetitive peak forward current	$I_{F,max}$	$T_c = 25^\circ C, t_p = 10 \mu\text{s}$	65	A
I^2t value	$\int I^2 dt$	$T_c = 25^\circ C, t_p = 10 \text{ ms}$	0.5	A^2s
Power dissipation	P_{tot}	$T_c = 25^\circ C$	64	W
Operating and storage temperature	T_j, T_{stg}		-55 to 210	$^\circ C$

Electrical Characteristics at $T_j = 210^\circ C$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Diode forward voltage	V_F	$I_F = 1 \text{ A}, T_j = 25^\circ C$	1.6			V
		$I_F = 1 \text{ A}, T_j = 210^\circ C$	2.6			
Reverse current	I_R	$V_R = 650 \text{ V}, T_j = 25^\circ C$	1			μA
		$V_R = 650 \text{ V}, T_j = 210^\circ C$	5		50	
Total capacitive charge	Q_c	$I_F \leq I_{F,MAX}$	7			nC
Switching time	t_s	$dI_F/dt = 200 \text{ A}/\mu\text{s}$				ns
		$T_j = 210^\circ C$			< 17	
Total capacitance	C	$V_R = 1 \text{ V}, f = 1 \text{ MHz}, T_j = 25^\circ C$	76			pF
		$V_R = 400 \text{ V}, f = 1 \text{ MHz}, T_j = 25^\circ C$	12			
		$V_R = 650 \text{ V}, f = 1 \text{ MHz}, T_j = 25^\circ C$	12			

Thermal Characteristics

Thermal resistance, junction - case	R_{thJC}	3.55	$^\circ C/W$
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Mechanical Properties

Mounting torque	M	0.6	Nm
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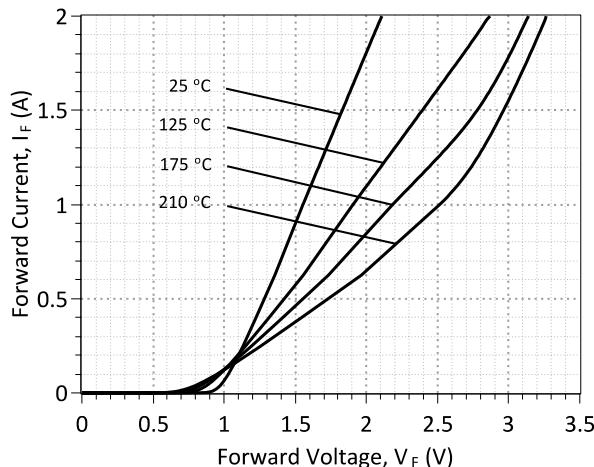


Figure 1: Typical Forward Characteristics

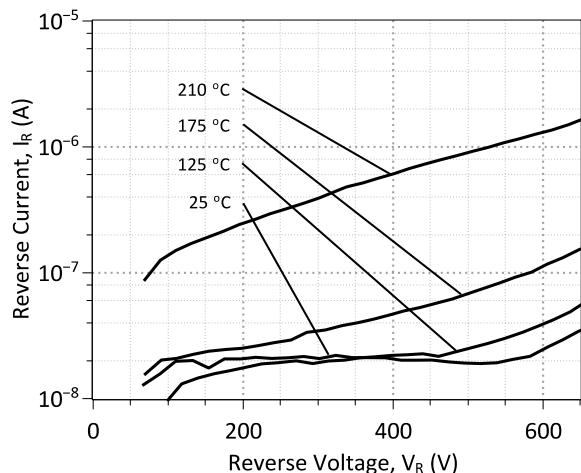


Figure 2: Typical Reverse Characteristics

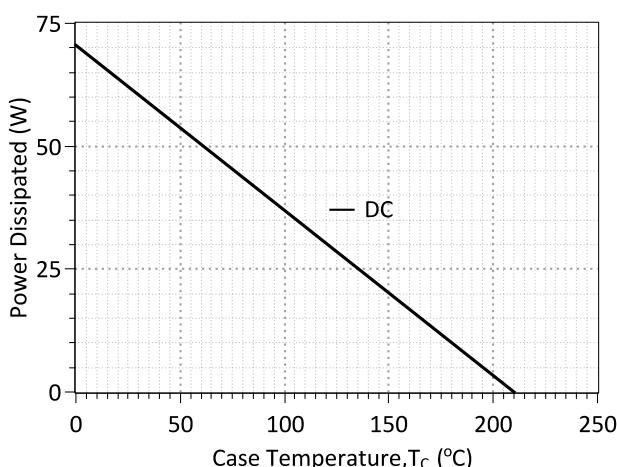


Figure 3: Power Derating Curve

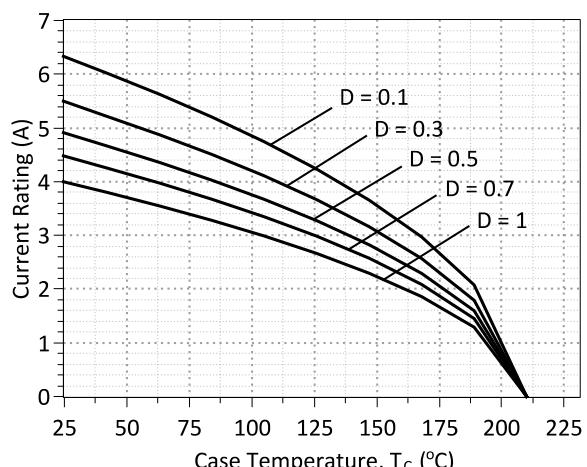


Figure 4: Current Derating Curves ($D = t_p/T$, $t_p = 400 \mu s$)
 (Considering worst case Z_{th} conditions)

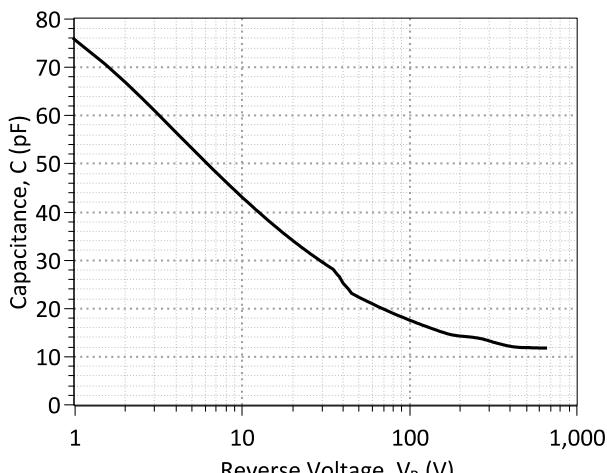


Figure 5: Typical Junction Capacitance vs Reverse Voltage Characteristics

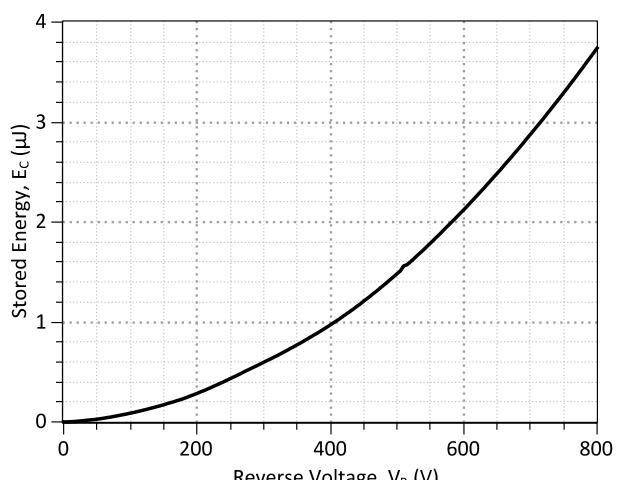


Figure 6: Typical Capacitive Energy vs Reverse Voltage Characteristics

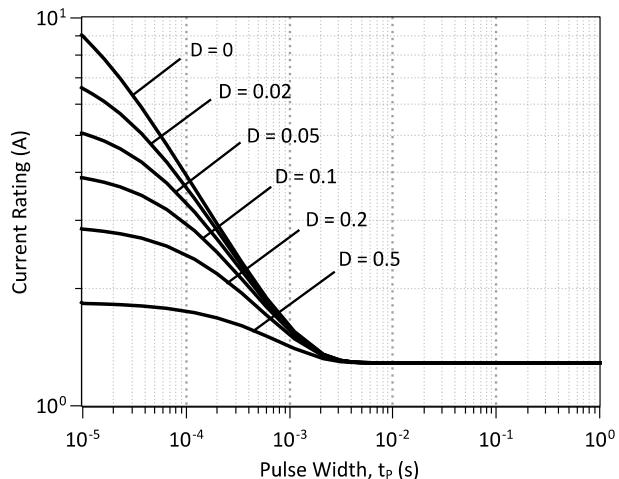


Figure 7: Current vs Pulse Duration Curves at $T_c = 190 \text{ } ^\circ\text{C}$

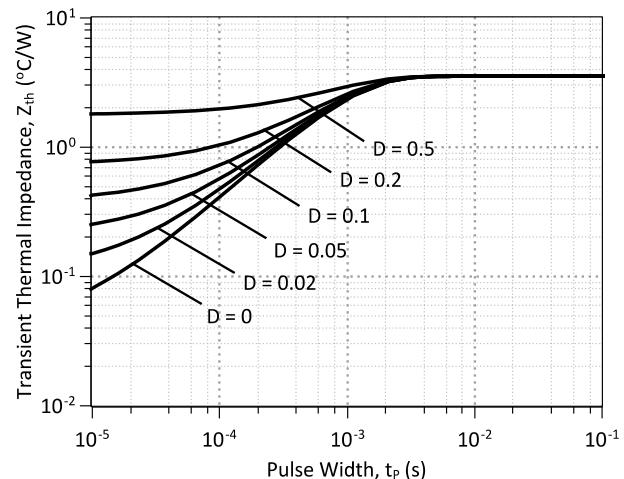
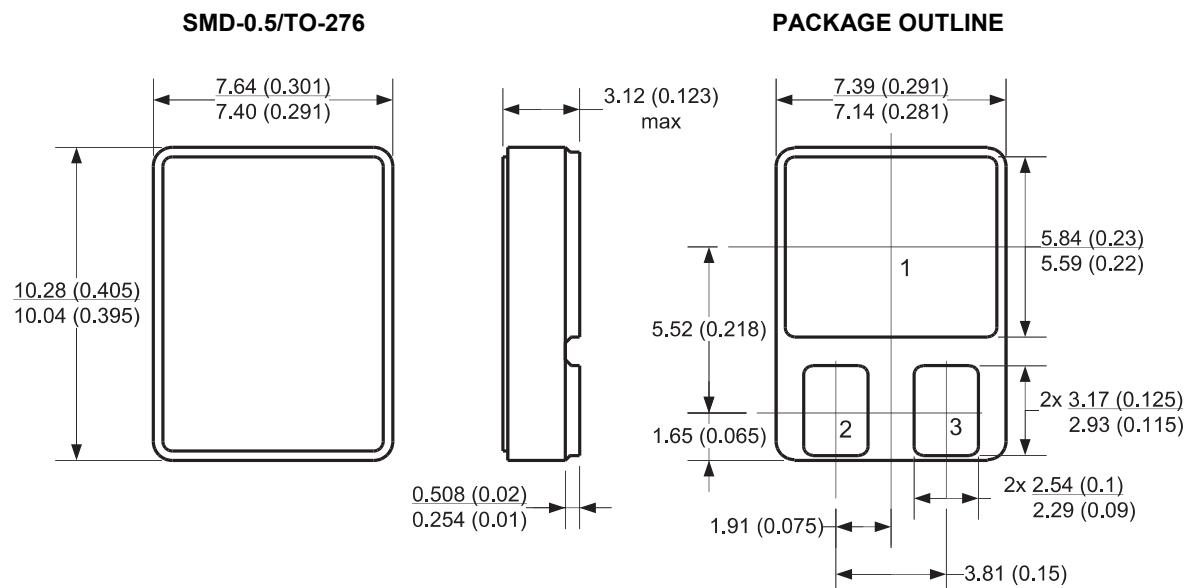


Figure 8: Transient Thermal Impedance

Package Dimensions:



NOTE

1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS

Revision History			
Date	Revision	Comments	Supersedes
2014/08/26	1	Updated Electrical Characteristics	
2012/04/24	0	Initial release	

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SPICE Model Parameters

This is a secure document. Copy this code from the SPICE model PDF file on our website into a SPICE software program for simulation of the 1N8031-GA.

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* MODEL OF GeneSiC Semiconductor Inc.
*
* $Revision: 1.0      $
* $Date: 05-SEP-2013      $
*
* GeneSiC Semiconductor Inc.
* 43670 Trade Center Place Ste. 155
* Dulles, VA 20166
*
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* These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
* OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
* TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
* PARTICULAR PURPOSE."
* Models accurate up to 2 times rated drain current.
*
* Start of 1N8031-GA SPICE Model
*
.SUBCKT 1N8031 ANODE KATHODE
D1 ANODE KATHODE 1N8031_25C; Call the Schottky Diode Model
D2 ANODE KATHODE 1N8031_PIN; Call the PiN Diode Model
.MODEL 1N8031_25C D
+ IS      3.57E-18      RS      0.49751
+ TRS1    0.0057      TRS2    2.40E-05
+ N       1      IKF      322
+ EG      1.2      XTI      3
+ CJO     9.12E-11      VJ      0.371817384
+ M       1.527759838      FC      0.5
+ TT      1.00E-10      BV      650
+ IBV     1.00E-03      VPK     650
+ IAVE    1      TYPE    Sic_Schottky
+ MFG    GeneSiC_Semiconductor
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+ EG      3.23      XTI     -14
+ FC      0.5      TT      0
+ BV      650      IBV     1.00E-03
+ VPK     650      IAVE     1
+ TYPE    Sic_Pin
.ENDS
*
* End of 1N8031-GA SPICE Model
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